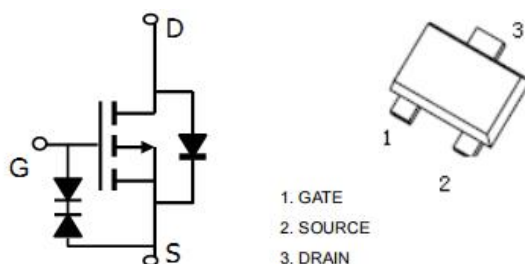


**SOT-723 -20V P Channel Enhancement ESD Protection 沟道增强型带静电保护
MOS Field Effect Transistor 场效应管**



■ **Absolute Maximum Ratings 最大额定值**

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	-20	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 12	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_A = 25^\circ C$)	-0.66	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	-1.2	A
Total Device Dissipation 总耗散功率	P_D (at $T_A = 25^\circ C$)	150	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	850	$^\circ C/W$
ESD Protected Up to 人体模式静电保护范围	ESD(HBM)	2.0	kV
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ C$

■ **Device Marking 产品字标**

FS3139KT7=KD/2H

Electrical Characteristics 电特性

 (T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D = -250uA, V _{GS} =0V)	BV _{DSS}	-20	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D = -250uA, V _{GS} = V _{DS})	V _{GS(th)}	-0.4	-0.7	-1	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} = -20V)	I _{DSS}	—	—	-1	μA
Gate Body Leakage 栅极漏电流(V _{GS} =±12V, V _{DS} =0V)	I _{GSS}	—	—	±10	μA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D = -0.5A, V _{GS} = -4.5V) (I _D = -0.2A, V _{GS} = -2.5V)	R _{DS(ON)}	—	530 750	560 780	mΩ
Diode Forward Voltage Drop 内附二极管压降(I _{SD} = -0.5A, V _{GS} =0V)	V _{SD}	—	—	-1	V
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} = -10V, f=1MHz)	C _{ISS}	—	33	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} = -10V, f=1MHz)	C _{OSS}	—	9	—	pF
Reverse Transfer Capacitance 反馈电容(V _{GS} =0V, V _{DS} = -10V, f=1MHz)	C _{RSS}	—	3	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} = -10V, I _D = -150mA, V _{GS} =10V)	Q _g	—	1.7	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} = -10V, I _D = -150mA, V _{GS} =10V)	Q _{gs}	—	0.57	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} = -10V, I _D = -150mA, V _{GS} =10V)	Q _{gd}	—	0.25	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} = -10V I _D = -200mA, R _{GEN} =10Ω, V _{GS} = -4.5V)	t _{d(on)}	—	7	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} = -10V I _D = -200mA, R _{GEN} =10Ω, V _{GS} = -4.5V)	t _r	—	84	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} = -10V I _D = -200mA, R _{GEN} =10Ω, V _{GS} = -4.5V)	t _{d(off)}	—	840	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} = -10V I _D = -200mA, R _{GEN} =10Ω, V _{GS} = -4.5V)	t _f	—	640	—	ns

■ Typical Characteristic Curve 典型特性曲线

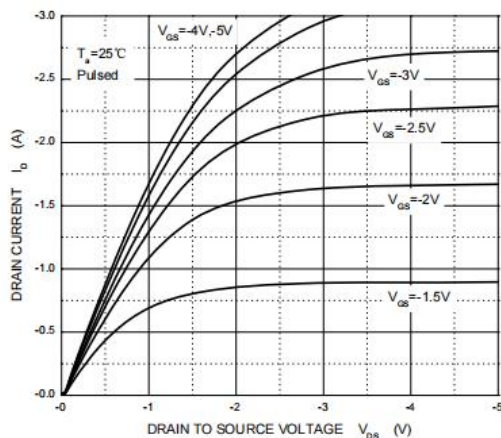


Figure 1: Output Characteristics

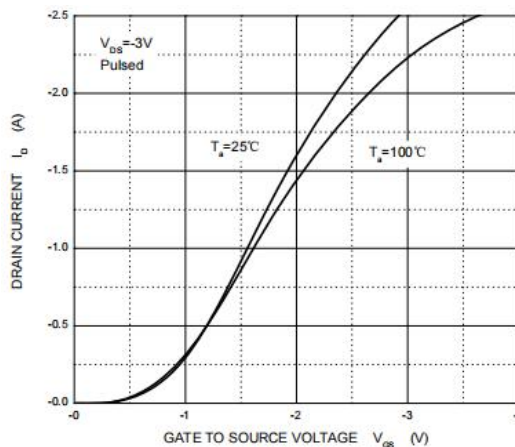


Figure 2: Transfer Characteristics

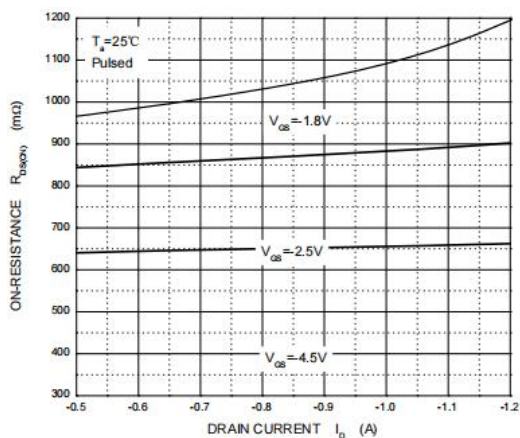


Figure 3: On-Resistance vs. Drain Current

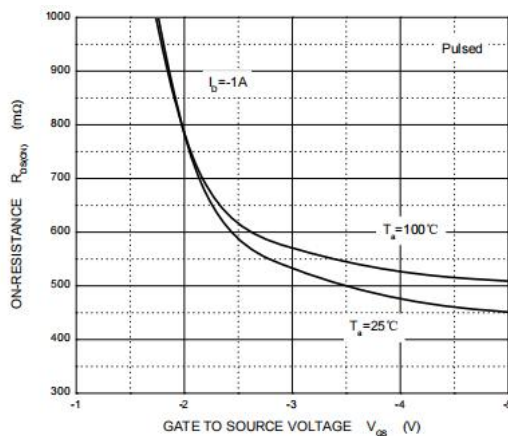


Figure 4: On-Resistance vs. V_{GS}

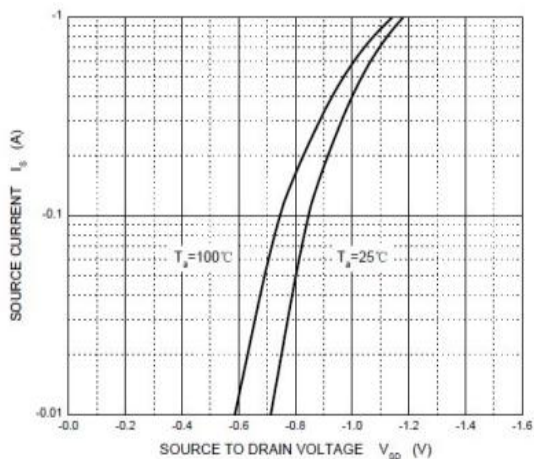


Figure 5: Diode Characteristics

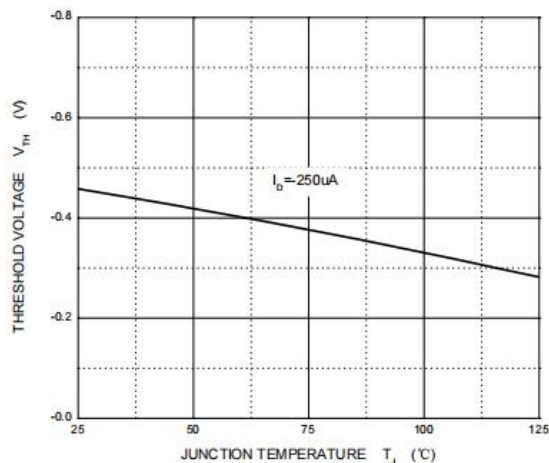
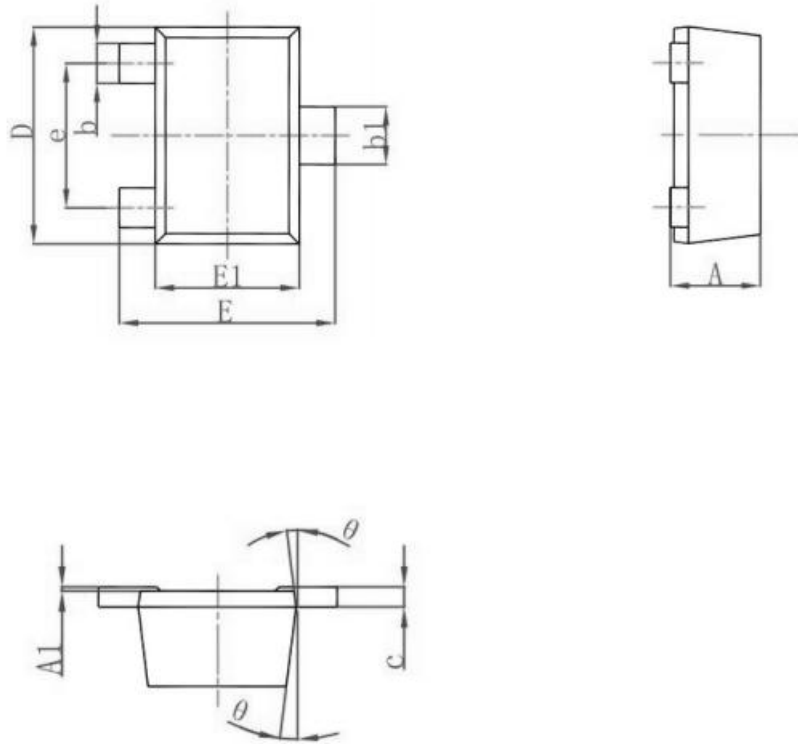


Figure 6: Threshold Characteristics

■ **Dimension** 外形封装尺寸



Symbol	Dimensions In Millimet	
	Min	Max
A	0.40	0.50
A1	0.00	0.10
b	0.15	0.25
b1	0.20	0.30
c	0.06	0.16
D	1.10	1.30
e	0.8TYP	
E	1.10	1.30
E1	0.70	0.90
θ	8°	10°